

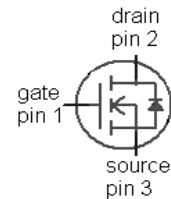
OptiMOS™ 3 Power-Transistor
Features

- Fast switching MOSFET for SMPS
- Optimized technology for DC/DC converters
- Qualified according to JEDEC¹⁾ for target applications
- N-channel, logic level
- Excellent gate charge x $Q_{DS(on)}$ product (FOM)
- Very low on-resistance $r_{DS(on)}$
- Avalanche rated
- Pb-free plating; RoHS compliant
- Halogen-free according to IEC61249-2-21

Product Summary

V_{DS}	30	V
$Q_{DS(on),max}$	9.6	mC
I_D	35	A

Type	IPP096N03L G	IPB096N03L G
Package	PG-TO220-3-1	PG-TO263-3
Marking	096N03L	096N03L


Maximum ratings, at $T_j=25\text{ °C}$, unless otherwise specified

Parameter	Symbol	Conditions	Value	Unit
Continuous drain current	I_D	$V_{GS}=10\text{ V}$, $T_C=25\text{ °C}$	35	A
		$V_{GS}=10\text{ V}$, $T_C=100\text{ °C}$	35	
		$V_{GS}=4.5\text{ V}$, $T_C=25\text{ °C}$	35	
		$V_{GS}=4.5\text{ V}$, $T_C=100\text{ °C}$	30	
Pulsed drain current ²⁾	$I_{D,pulse}$	$T_C=25\text{ °C}$	245	
Avalanche current, single pulse ³⁾	I_{AS}	$T_C=25\text{ °C}$	35	
Avalanche energy, single pulse	E_{AS}	$I_D=12\text{ A}$, $V_{GS}=25\text{ V}$	40	mJ
Reverse diode dI/dt	dI/dt	$I_D=35\text{ A}$, $V_{DS}=24\text{ V}$, $dI/dt=200\text{ A}/\mu\text{s}$, $T_{j,max}=175\text{ °C}$	6	kV/ μs
Gate source voltage	V_{GS}		± 20	V

¹⁾ J-STD20 and JESD22

Maximum ratings, at $T_j=25\text{ °C}$, unless otherwise specified

Parameter	Symbol	Conditions	Value	Unit
Power dissipation	$R_{\theta\text{tot}}$	$T_c=25\text{ °C}$	42	W
Operating and storage temperature	T_j, T_{stg}		-55 ... 175	°C
IEC climatic category; DIN IEC 68-1			55/175/56	

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	

Thermal characteristics

Thermal resistance, junction - case	$R_{\theta\text{JC}}$		-	-	3.6	K/W
SMD version, device on PCB	$R_{\theta\text{JA}}$	minimal footprint	-	-	62	
		6 cm ² cooling area ⁴⁾	-	-	40	

Electrical characteristics, at $T_j=25\text{ °C}$, unless otherwise specified

Static characteristics

Drain-source breakdown voltage	$V_{\text{BR(DSS)}}$	$V_{\text{GS}}=0\text{ V}, I_{\text{D}}=1\text{ mA}$	30	-	-	V
Gate threshold voltage	$V_{\text{GS(th)}}$	$V_{\text{DS}}=V_{\text{GS}}, I_{\text{D}}=250\text{ }\mu\text{A}$	1	-	2.2	
Zero gate voltage drain current	I_{DSS}	$V_{\text{DS}}=30\text{ V}, V_{\text{GS}}=0\text{ V}, T_j=25\text{ °C}$	-	0.1	1	μA
		$V_{\text{DS}}=30\text{ V}, V_{\text{GS}}=0\text{ V}, T_j=125\text{ °C}$	-	10	100	
Gate-source leakage current	I_{GSS}	$V_{\text{GS}}=20\text{ V}, V_{\text{DS}}=0\text{ V}$	-	10	100	nA
Drain-source on-state resistance ⁵⁾	$R_{\text{DS(on)}}$	$V_{\text{GS}}=4.5\text{ V}, I_{\text{D}}=30\text{ A}$	-	11.3	14.1	$\text{m}\Omega$
		$V_{\text{GS}}=10\text{ V}, I_{\text{D}}=30\text{ A}$	-	8.0	9.6	
Gate resistance	R_{G}		-	1.1	-	Ω
Transconductance	g_{fs}	$ V_{\text{DS}} >2 V_{\text{GS}} , I_{\text{D}}=I_{\text{DS(on)max}}, I_{\text{G}}=0, I_{\text{S}}=30\text{ A}$	26	53	-	S

²⁾ See figure 3 for more detailed information







³⁾ See figure 13 for more detailed information

⁴⁾ Device on 40 mm x 40 mm x 1.5 mm epoxy PCB FR4 with 6 cm² (one layer, 70 μm thick) copper area for drain connection. PCB is vertical in still air.









⁵⁾ Measured from drain tab to source pin

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	


Dynamic characteristics

Input capacitance		$\boxed{V}_{GS}=0\text{ V}, \boxed{V}_{DS}=15\text{ V},$ $f=1\text{ MHz}$	-	1200	1600	pF
Output capacitance			-	500	660	
Reverse transfer capacitance	C_{rss}		-	24	-	
Turn-on delay time		$\boxed{V}_{DD}=15\text{ V}, \boxed{V}_{GS}=10\text{ V},$ $I_D=30\text{ A}, R_G=1.6\ \Omega$	-	4.0	-	ns
Rise time			-	3.2	-	
Turn-off delay time			-	16	-	
Fall time			-	2.6	-	

Gate Charge Characteristics⁵⁾

Gate to source charge		$\boxed{V}_{DD}=15\text{ V}, I_D=30\text{ A},$ $\boxed{V}_{GS}=0\text{ to }4.5\text{ V}$	-	4.0	-	nC
Gate charge at threshold			-	1.9	-	
Gate to drain charge			-	1.8	-	
Switching charge			-	3.9	-	
Gate charge total			-	7.4	-	
Gate plateau voltage	$\boxed{V}_{plateau}$		-	3.4	-	
Gate charge total		$\boxed{V}_{DD}=15\text{ V}, I_D=30\text{ A},$ $\boxed{V}_{GS}=0\text{ to }10\text{ V}$	-	15	-	nC
Gate charge total, sync. FET		$\boxed{V}_{DS}=0.1\text{ V},$ $\boxed{V}_{GS}=0\text{ to }4.5\text{ V}$	-	6.4	-	
Output charge		$\boxed{V}_{DD}=15\text{ V}, \boxed{V}_{GS}=0\text{ V}$	-	13	-	

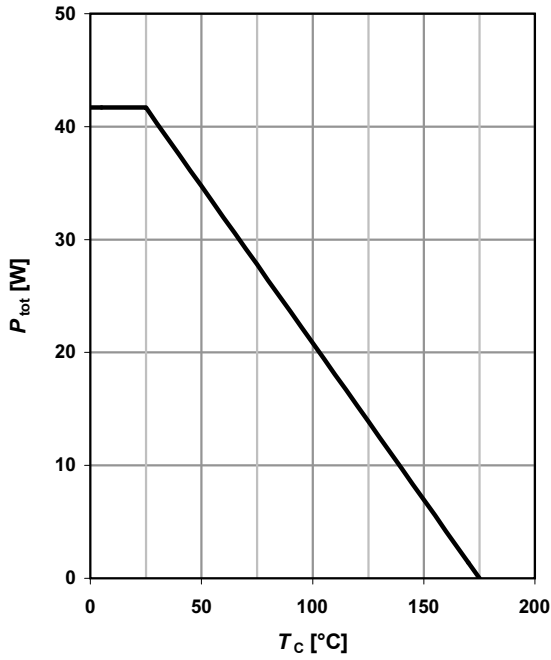
Reverse Diode

Diode continuous forward current	I_{S}	$\vartheta_C=25\text{ }^\circ\text{C}$	-	-	35	A
Diode pulse current	$I_{S,pulse}$		-	-	245	
Diode forward voltage	\boxed{V}_{SD}	$\boxed{V}_{GS}=0\text{ V}, I_P=30\text{ A},$ $\vartheta_j=25\text{ }^\circ\text{C}$	-	0.94	1.2	V
Reverse recovery charge		$\boxed{V}_R=15\text{ V}, I_P=I_S,$ $dI/dt \leq 400\text{ A}/\mu\text{s}$	-	-	10	nC

⁵⁾ See figure 16 for gate charge parameter definition

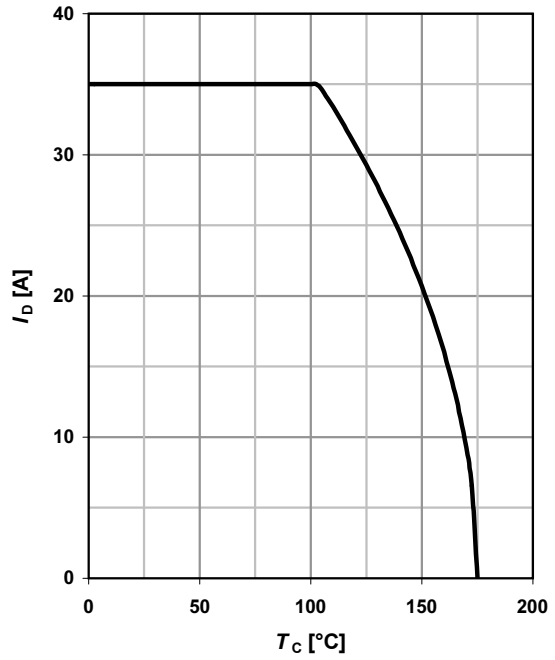
1 Power dissipation

$P_{tot} = f(T_c)$



2 Drain current

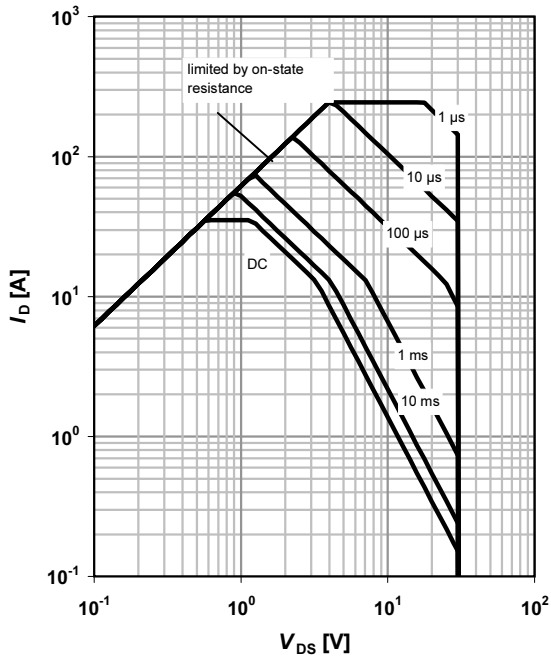
$I_D = f(T_c); V_{GS} \geq 10 V$



3 Safe operating area

$I_D = f(V_{DS}); T_c = 25^\circ C; \rho \geq 0$

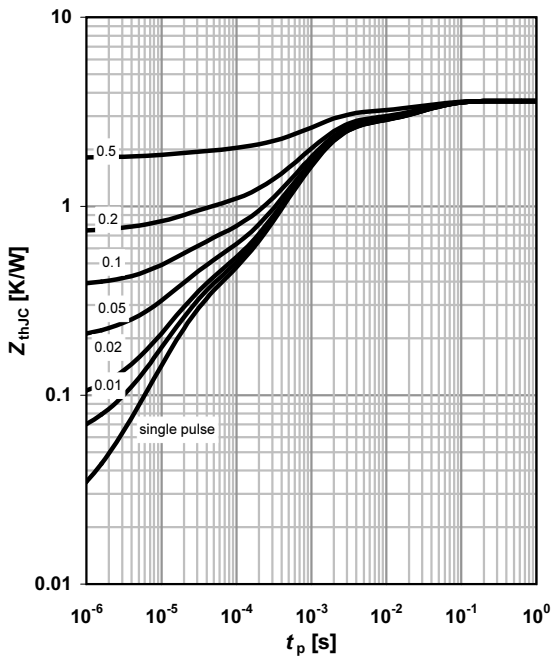
parameter: ρ



4 Max. transient thermal impedance

$Z_{thJC} = f(t_p)$

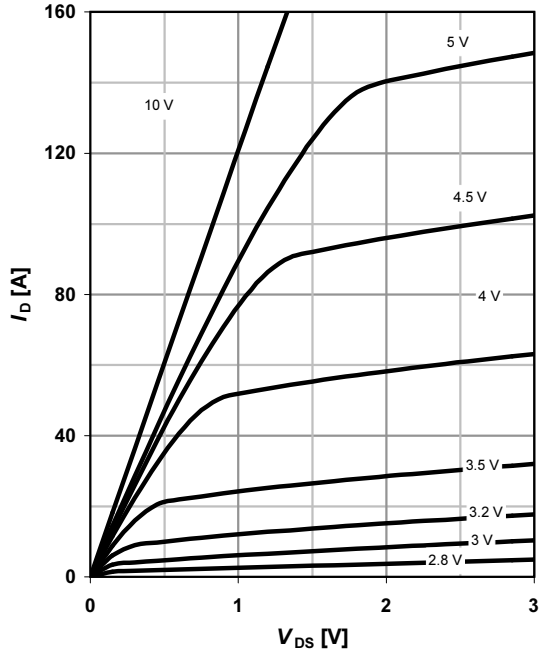
parameter: $\rho \geq$



5 Typ. output characteristics

$$I_D = f(V_{DS}); j = 25^\circ\text{C}$$

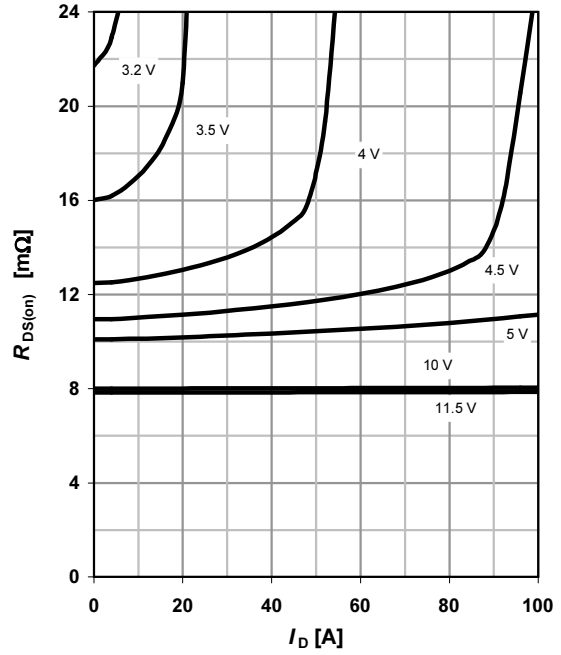
parameter: V_{GS}



6 Typ. drain-source on resistance

$$R_{DS(on)} = f(I_D); j = 25^\circ\text{C}$$

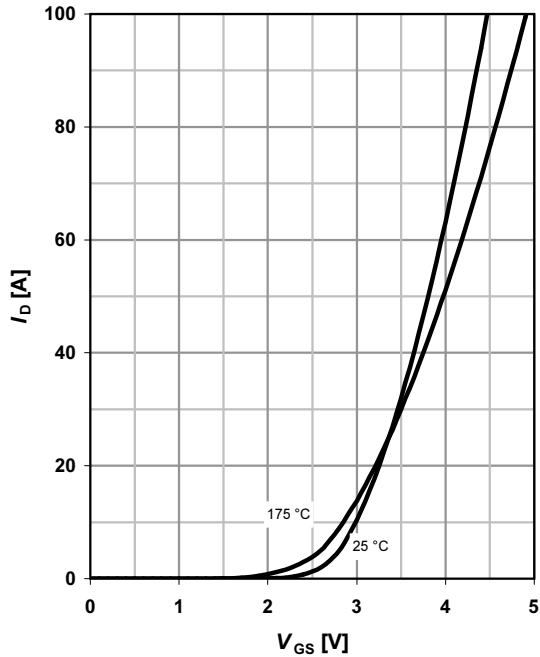
parameter: V_{GS}



7 Typ. transfer characteristics

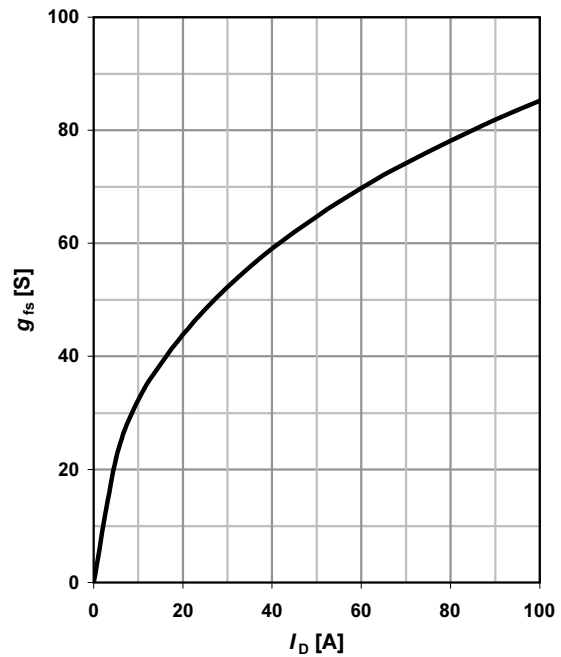
$$I_D = f(V_{GS}); |V_{DS}| > 2 |V_{DS(on)max}|$$

parameter: j



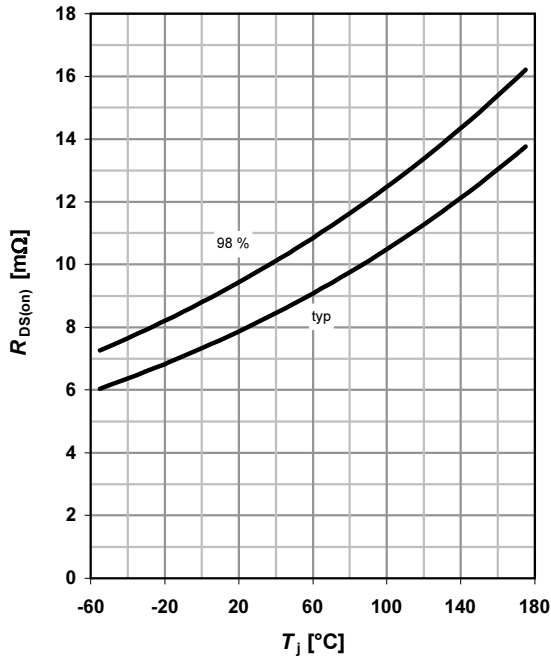
8 Typ. forward transconductance

$$g_{fs} = f(I_D); j = 25^\circ\text{C}$$



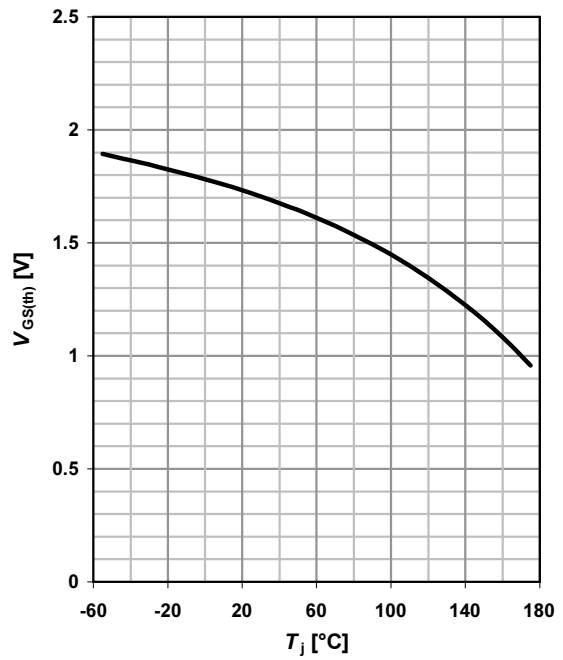
9 Drain-source on-state resistance

$R_{DS(on)} = f(T_j)$; $I_D = 30 \text{ A}$; $V_{GS} = 10 \text{ V}$



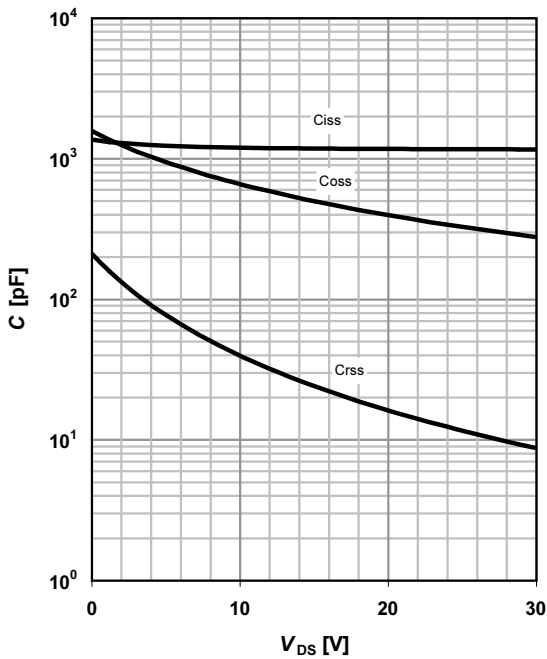
10 Typ. gate threshold voltage

$V_{GS(th)} = f(T_j)$; $V_{GS} = V_{DS}$; $I_D = 250 \mu\text{A}$



11 Typ. capacitances

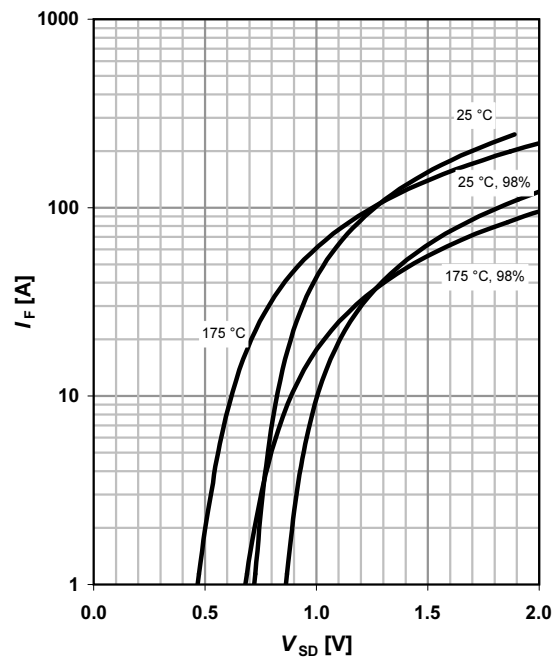
$C = f(V_{DS})$; $V_{GS} = 0 \text{ V}$; $f = 1 \text{ MHz}$



12 Forward characteristics of reverse diode

$I_F = f(V_{SD})$

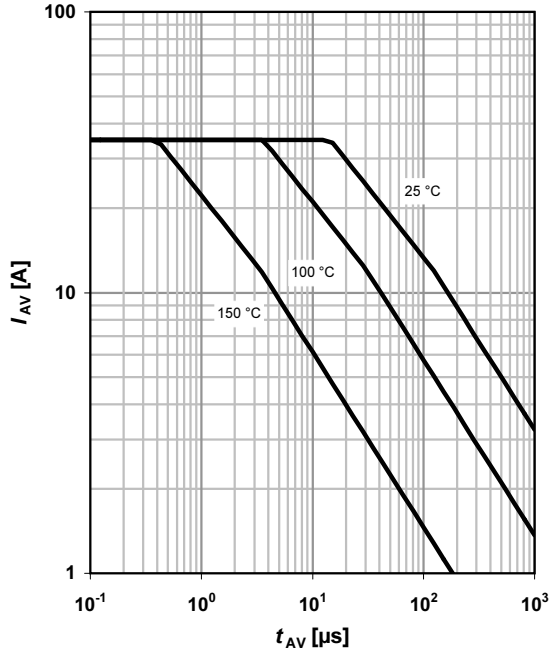
parameter: T_j



13 Avalanche characteristics

$I_{AS} = f(I_{AV}); V_{GS} = 25 \geq$

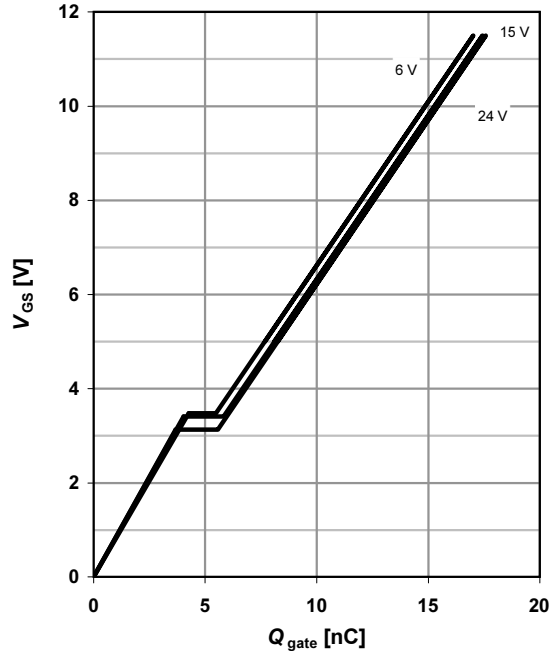
parameter: $i_{j(start)}$



14 Typ. gate charge

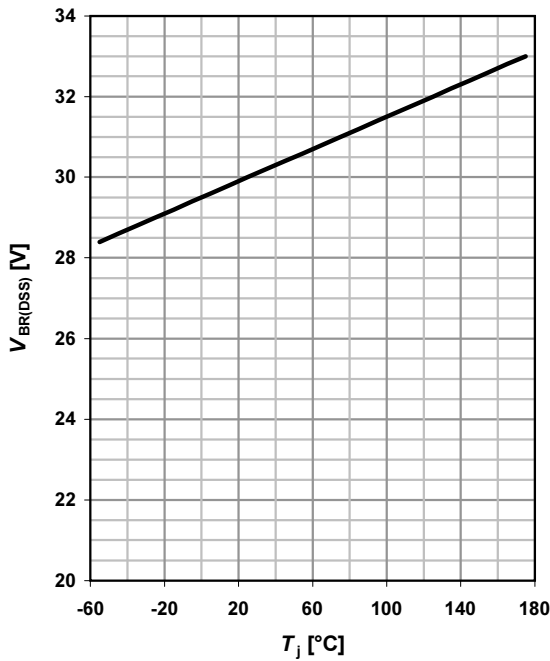
$V_{GS} = f(Q_{gate}); I_D = 30 \text{ A pulsed}$

parameter: i_{DD}

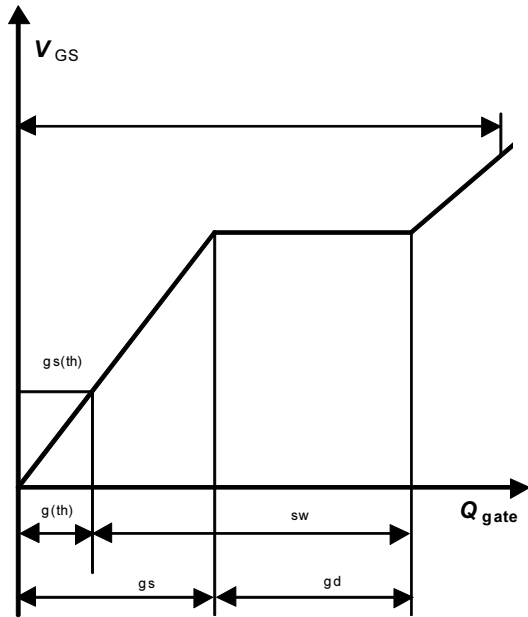


15 Drain-source breakdown voltage

$V_{BR(DSS)} = f(T_j); I_D = 1 \text{ mA}$

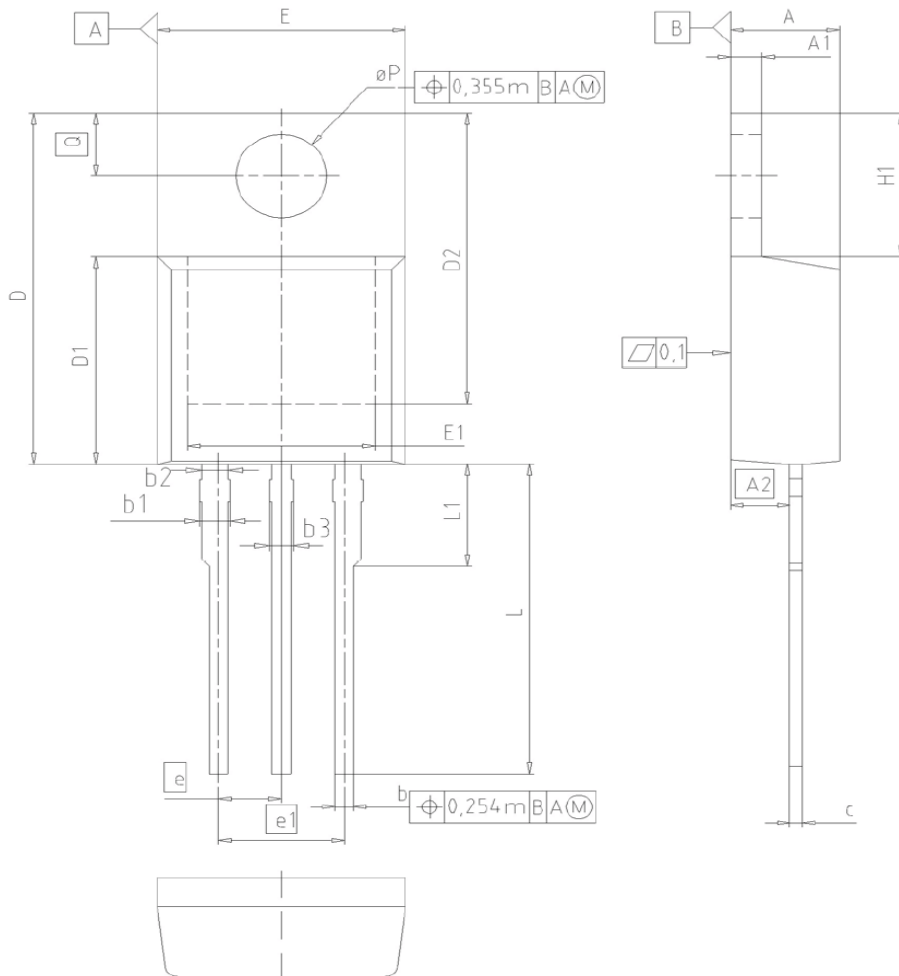


16 Gate charge waveforms



Package Outline

PG-TO220-3-1



DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4.30	4.57	0.169	0.180
A1	1.17	1.40	0.046	0.055
A2	2.15	2.72	0.085	0.107
b	0.65	0.86	0.026	0.034
b1	0.95	1.40	0.037	0.055
b2	0.95	1.15	0.037	0.045
b3	0.65	1.15	0.026	0.045
c	0.33	0.60	0.013	0.024
D	14.81	15.95	0.583	0.628
D1	8.51	9.45	0.335	0.372
D2	12.19	13.10	0.480	0.516
E	9.70	10.36	0.382	0.408
E1	6.50	8.60	0.256	0.339
e	2.54		0.100	
e1	5.08		0.200	
N	3		3	
H1	5.90	6.90	0.232	0.272
L	13.00	14.00	0.512	0.551
L1	-	4.80	-	0.189
øP	3.60	3.89	0.142	0.153
Q	2.60	3.00	0.102	0.118

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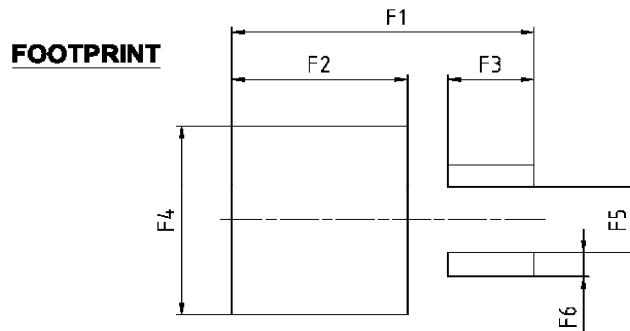
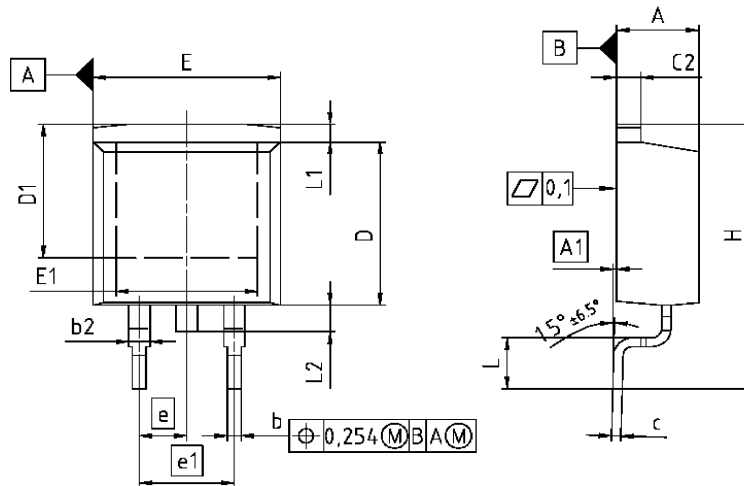
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ISSUE DATE
23-08-2007

REVISION
05

Package Outline

PG-TO263-3



DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4.300	4.572	0.169	0.180
A1	0.000	0.254	0.000	0.010
b	0.650	0.850	0.026	0.033
b2	0.950	1.321	0.037	0.052
c	0.330	0.650	0.013	0.026
c2	0.170	1.400	0.046	0.055
D	8.509	9.450	0.335	0.372
D1	7.100	-	0.280	-
E	9.800	10.312	0.386	0.406
E1	6.500	-	0.256	-
e	2.540		0.100	
e1	5.080		0.200	
N	2		2	
H	14.605	15.875	0.575	0.625
L	2.200	3.000	0.087	0.118
L1	-	1.600	-	0.063
L2	1.000	1.778	0.039	0.070
F1	16.050	16.250	0.632	0.640
F2	9.300	9.500	0.366	0.374
F3	4.500	4.700	0.177	0.185
F4	10.700	10.900	0.421	0.429
F5	3.630	3.830	0.143	0.151
F6	1.100	1.300	0.043	0.051

REFERENCE
JEDEC TO263

SCALE

EUROPEAN PROJECTION

ISSUE DATE
12-02-2006

FILE
TO263_2

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Infineon Technologies AG
81726 München, Germany
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